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Front-end circuits






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References:

- U. Tietze, Ch.Schenk, Electronics Circuits – Handbook for Design and Applications, Springer, 2008
- J.P. Bentley, Principles of measurement system, Pearson Education, 4th ed.
- Application notes of:
 - Analog Devices,
 - Linear Technology (now AD)
 - Texas Instruments,
 - National Semiconductors (now TI)
 - Burr-Brown (now TI)
 - ON Semi (now with Fairchild Semiconductor)



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Outline:

- operational amplifier
 - VV- voltage/voltage amp – review
 - CV – current/voltage
 - VC – voltage/current
 - CC – current/current
- electrometer
- charge amplifier
- chopped amp and parametric modulation amp
- auto-zero amp

VV OPA

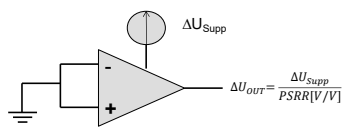
$V_{OUT} = (V_P - V_N)k_{uD}$

VV OPA - CMRR

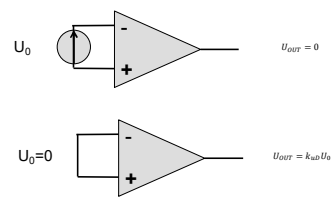
VV OPA - CMRR

$V_{out} = A_v V_{DIFF} + \frac{A_v}{CMRR} V_{CM}$

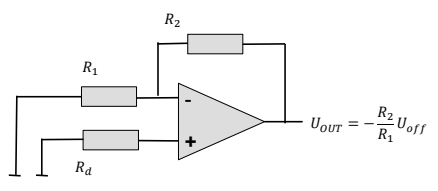
VV OPA - PSRR



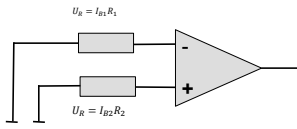
VV OPA - offset voltage



VV OPA - CMRR



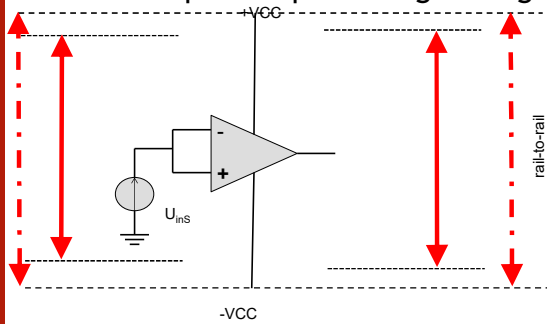
VV OPA - polarization/offset current



$$U_{off} = \frac{U_{OUT}}{k_{uD}} = (I_{B1}R_1 - I_{B2}R_2) \approx I_{Boff}R_{av} + I_B\Delta R$$

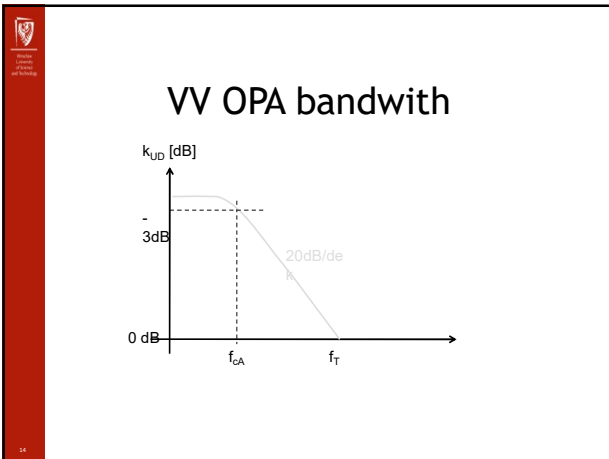
Offset of a system Chalkboard

VV OPA - input/output voltage swing



VV OPA - slew rate - SR

$\max\left(\frac{dU}{dt}\right) = 2nfU_{\max}$
 $\frac{dU}{dt} > SR = \left(\frac{dU_{out}}{dt}\right)_{\max}$
 $\frac{dU}{dt} < SR = \left(\frac{dU_{out}}{dt}\right)_{\max}$
 $SR = \frac{dU_{\max}}{dt} = 2nfU_{out\max}$
 $\frac{SR}{2\pi U_{out\max P}}$



- Basic parameters:**
1. Offset
 2. CMRR
 3. PSRR
 4. Output & Input swing
 5. Bandwidth

VV OPA

$U_{OUT} = (U_P - U_N)k_{uD}$

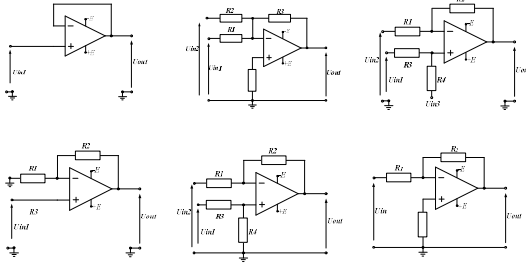
inverting amplifier

$K_u = \frac{U_{out}}{U_{in}} = -\frac{R_2}{R_1}$

Noninverted amplifier

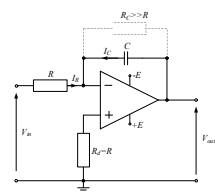
$K_u = \frac{U_{out}}{U_{in}} = 1 + \frac{R_2}{R_1}$

Numerical solutions



Calculations on the board

Integrator



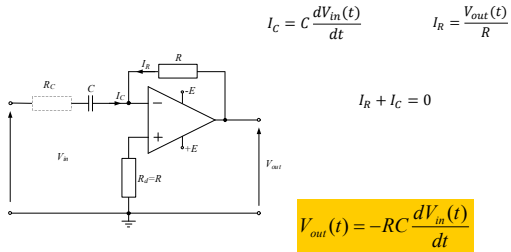
$$I_R = \frac{V_{in}(t)}{R} \quad I_C = C \frac{dV_{out}(t)}{dt}$$

$$I_R + I_C = 0$$

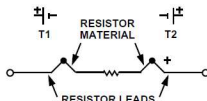
$$V_{out}(t) = -\frac{1}{RC} \int V_{in}(t) dt + U_0$$

$$V_{out} = -\frac{V_{in}}{R_1 C} t + U_0$$

Differentiator



Application tips gain and offset drift



Error (voltage offset) is due to temperature difference of resistor (or any other component) terminals.

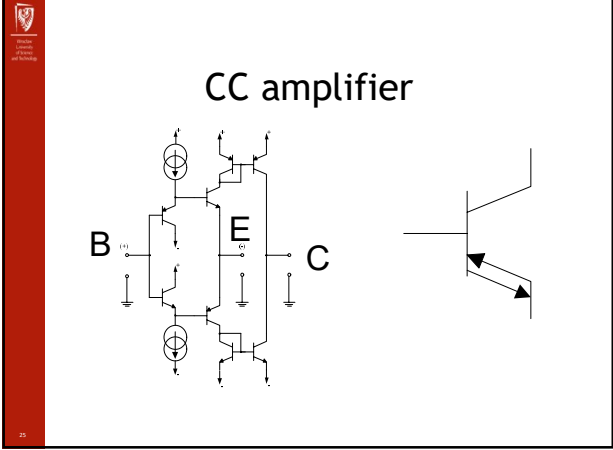
- TYPICAL RESISTOR THERMO-COUPLE EMFs**
- CARBON COMPOSITION 400 μ V/°C
 - METAL FILM 20 μ V/°C
 - EVENOHM OR MANGANIN WIRE-WOUND 2 μ V/°C
 - RCD COMPONENTS HP-SERIES 0.05 μ V/°C

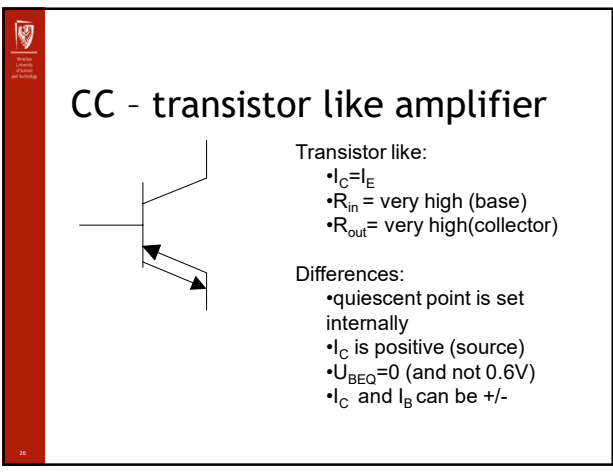
Application tips RTI vs. RTO errors

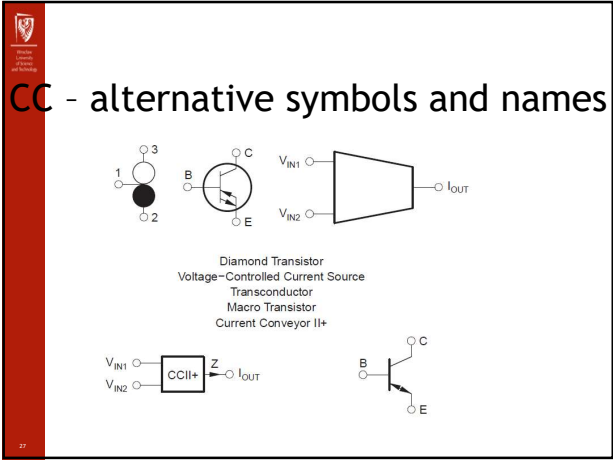
Total Error, RTI = Input Error + (Output Error/Gain)
Total Error, RTO = (Gain * Input Error) +

VOLTAGE OFFSET	(Total RTI Error = V _{OSI} + V _{OSO} /G)		
Input Offset, V _{OSI}	V _S = ± 5 V to ± 15 V	30	125
Over Temperature	V _S = ± 5 V to ± 15 V		185
Average TC	V _S = ± 5 V to ± 15 V	0.3	1.0
Output Offset, V _{OSO}	V _S = ± 15 V	400	1000
Over Temperature	V _S = ± 5 V		1500
Average TC	V _S = ± 5 V to ± 15 V		2000
Offset Referred to the	V _S = ± 5 V to ± 15 V	5.0	15

Total Offset Error RTI = V_{OSI} + (V_{OSO}/G) = 30 μ V + (400 μ V/10) = 30 V + 40V = 70 μ V
Total Offset Error RTO = (G (V_{OSI})) + V_{OSO} = (10 (30 μ V)) + 400 μ V = 700 μ V







$$K_u = \frac{U_{out}}{U_{in}} = \frac{R_L}{R_E}$$

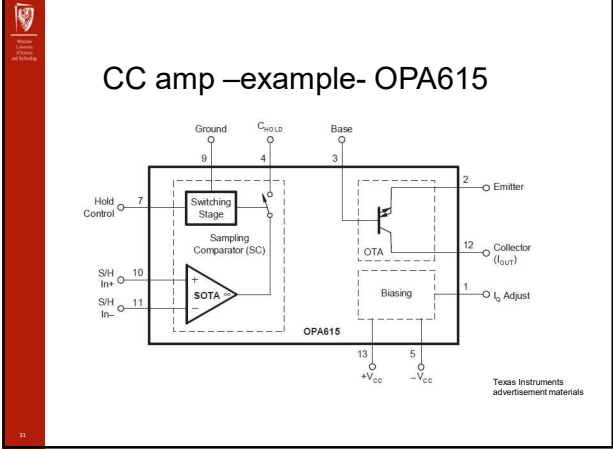
Tips:
 Ku positive (in transistor negative)
 Both R are small (10-1000Ω)

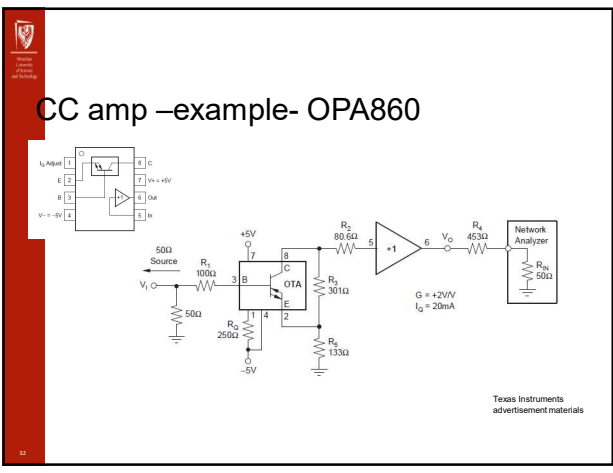
CC amp – application current feedback and current output

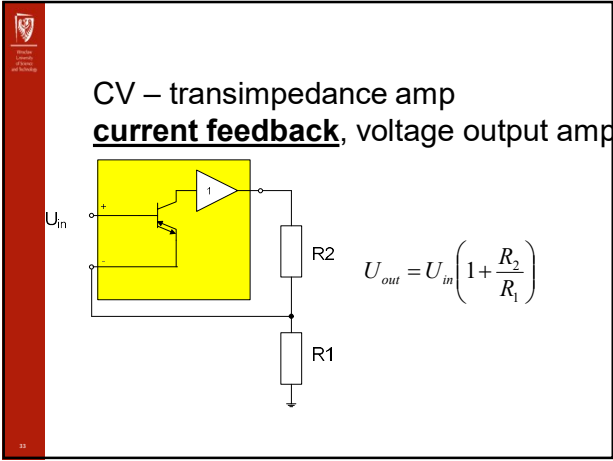
$$U_{out} = U_{in} \left(1 + \frac{R_2}{2R_1} \right)$$

CC amp - application

CC	Current amp
Example	OPA615
Applications	h.f. filters, laser drivers, line drivers, magnetic heads (hard discs)
Advantages	High bandwidth High slew rate
Disadvantages	Load dependent parameters
Offset	8 mV !!!!
Offset drift	40uV/deg
Bias current (+)	0,3uA
Large signal bandwidth	500MHz
Slew rate	3000V/us







CV amp

CV	Transimpedance amp
Example	AD8024
Applications	line drivers, LCD drivers, Sallen-Key active filter
Advantages	High bandwidth High slew rate
Disadvantages	Can be unstable with C or L load
Offset	2 mV !!!!
Offset drift	2uV/deg
Bias current (+)	1uA
Large signal bandwidth	350MHz
Slew rate	2400V/us

AD8011 current feedback amp

Gain	R _F (Ω)	R _O (Ω)	R _F (Ω)	Small Signal -3 dB BW (MHz), V _S = ±5 V
-1	1000	1000	52.3	150
-2	1000	499	54.9	130
-10	499	49.9	140	140
+1	1000		49.9	400
+2	1000	1000	49.9	250
+10	422	47.5	49.9	100
+6	1000	200	49.9	70
+6	500	100	49.9	170

VC – transconductance amp voltage feedback current output

$$U_{out} = U_{in} \left(1 + \frac{R_2}{R_1} \right)$$

VC – transconductance amp

VC	Transconductance amplifier
Example	MAX4445
Applications	Capacitive load
Advantages	Low offset and drift Stable with C load
Disadvantages	Load dependent gain
Offset	15 mV !!!!
Offset drift	12uV/deg
Bias current (+)	10uA
Large signal bandwidth	550MHz
Slew rate	5000V/us

VC – transconductance amp

On the board explanation

VV –traditional OPA

$$U_{out} = U_{in} \left(1 + \frac{R_2}{R_1} \right)$$

Current output

Voltage output

	Voltage feedback	Current feedback
Current output		
Voltage output		

TRANSCONDUCTANCE AMP

(VC)

$$I_{out} = (g_m U_{in(+)} - U_{in(-)}) k_u = \frac{U_{out}}{U_{in}} = \left(\frac{g_m R_1}{1 + g_m R_1 R_1 / (R_1 + R_2)} \right) \approx \left(1 + \frac{R_2}{R_1} \right)$$

TRANSIMPEDANCE AMP

$U_{out} = z_T I_{in}$ (CV) $\frac{U_{out}}{U_{in}} = \left(1 + \frac{R_2}{R_1}\right) \left(\frac{1}{1 + R_2/z_T}\right) \approx \left(1 + \frac{R_2}{R_1}\right)$

$z_T = \frac{R_T}{1 + j\frac{f}{f_g}} \Rightarrow f_{gf} = 1 + \frac{R_T}{R_2}$

The circuit diagram shows an operational amplifier in an inverting configuration. The input is a current source I_{in} connected to the inverting input through a resistor R_1 . The feedback path consists of a resistor R_2 and a capacitor C connected in parallel between the inverting input and the output. The non-inverting input is grounded. The output voltage is U_{out} .

The frequency response plots show the voltage gain k_u versus frequency f . The left plot shows a low-frequency gain of R_2/R_1 (marked with a red 'V') and a roll-off at the corner frequency f_g . The right plot shows a similar response but with a different gain and corner frequency, also marked with a red 'V'.

Transimpedance amp as photodiode front-end

The diagram shows a photodiode connected to the input of a transimpedance amplifier. The photodiode is represented by a current source I_{ph} in parallel with a diode symbol. The current I_{ph} flows into the inverting input of the op-amp, which is biased through a resistor R_1 . The feedback network consists of a resistor R_2 and a capacitor C connected in parallel between the inverting input and the output. The output voltage is U_{out} .

Electrometer

electronic device for charge or potential (voltage) measurements with very little leakage current, down to fA;

Used for example in measurements of:

- pH,
- redox potential (oxidation, reduction potential , ORP),
- ionization radiation (ionization chamber),
- piezosensors (e.g. acceleration),
-

Types of electrometers:

- Valve electrometer – use a special tube of leakage of fA;
- Solid state – with FET/MOSFET transistors;
- Vibrating capacitor – („parametric modulation”)

Electrometer problems:

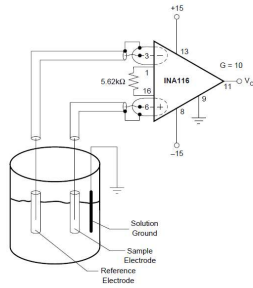
- Use of GΩ resistors (Vishay)
- Surface leakage (PCB on teflon, glass, cleaning problems, drying),
- Transistor/IC leakage,

High input impedance

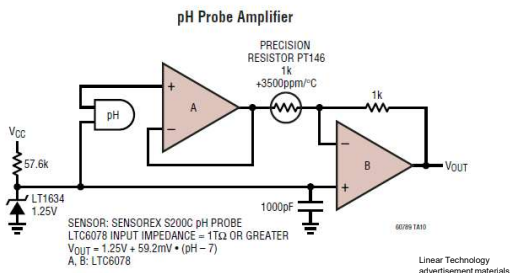
LS830 2 FET in common case:
 $I_G < 80\text{fA}$, $E_n < 70\text{nV}/\text{Hz}^{1/2}$, $C < 3\text{pF}$

Single FET:
 BF662 (3pA)
 2N4416 (C<1pF)

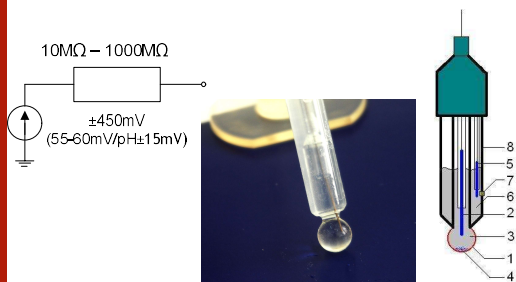
pH transducer



LTC6078/LTC6079 application example

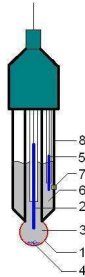


pH glass electrode construction

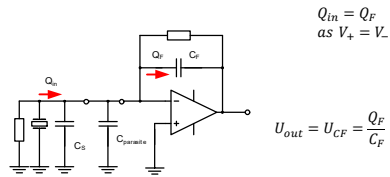


pH glass electrode construction

1. a sensing part of electrode, a bulb made from a specific glass
2. internal electrode, usually silver chloride electrode or calomel electrode
3. internal solution, usually a pH=7 buffered solution of 0.1 mol/L KCl for pH electrodes or 0.1 mol/L MeCl for pMe electrodes
4. when using the silver chloride electrode, a small amount of AgCl can precipitate inside the glass electrode
5. reference electrode, usually the same type as 2
6. reference internal solution, usually 0.1 mol/L KCl
7. junction with studied solution, usually made from ceramics or capillary with asbestos or quartz fiber.
8. body of electrode, made from non-conductive glass or plastics.



An idea of „charge amplifier”



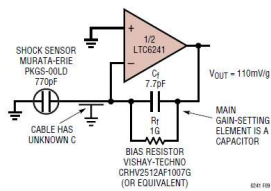
$$Q_{in} = Q_F$$

$$\text{as } V_+ = V_-$$

$$U_{out} = U_{CF} = \frac{Q_F}{C_F}$$


U_{out} is not depend on C_S nor $C_{parasite}$

LTC6241 „charge amplifier” (integrating amplifier)

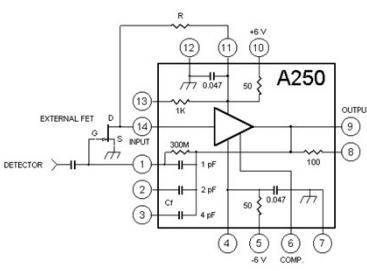


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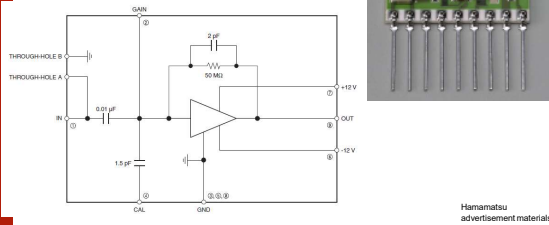
A250 Amptek charge amp




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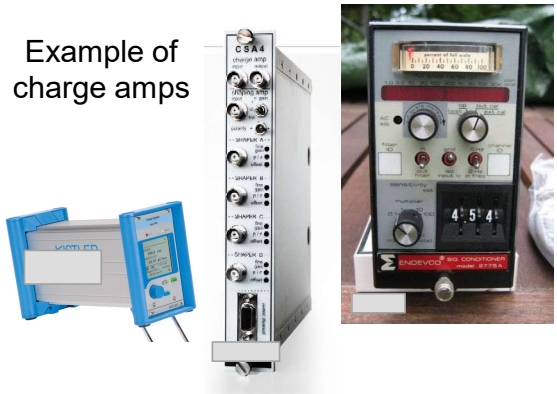
Hybrid charge amplifier

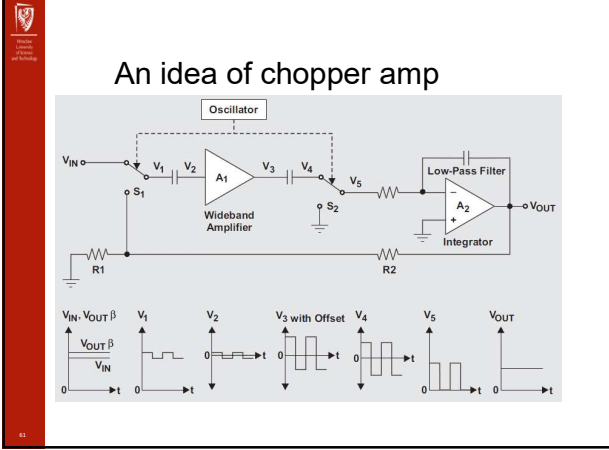


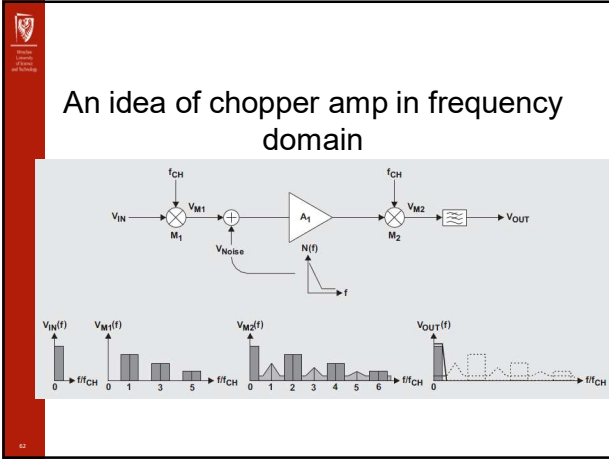
Hamamatsu
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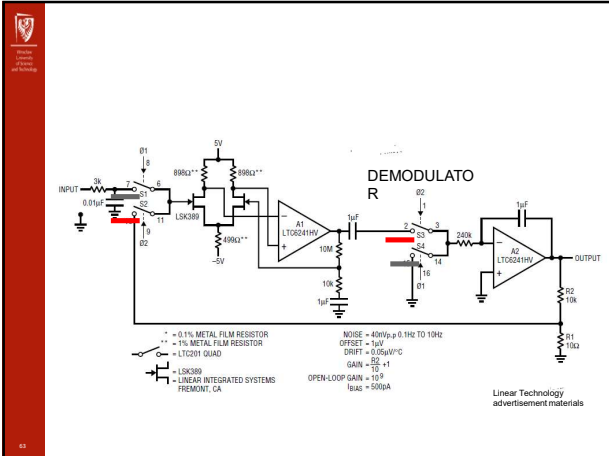

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Example of charge amps









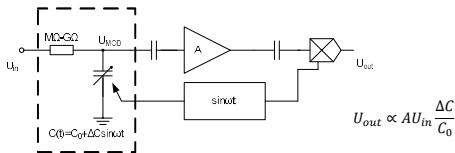


chopper amp drawbacks

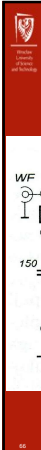
- the amplifier has a single-ended, noninverting input and cannot accept differential signals without additional circuitry at the front end,
- the carrier-based approach constitutes a sampled data system, and overall amplifier bandwidth is limited to a small fraction of the chopper frequency,
- the chopper frequency is restricted by ac amplifier gain-phase limitations and errors induced by switch response time,
- keeping the effects of these considerations small the chopper frequencies are therefore in the low-kilohertz range, dictating low overall bandwidth.



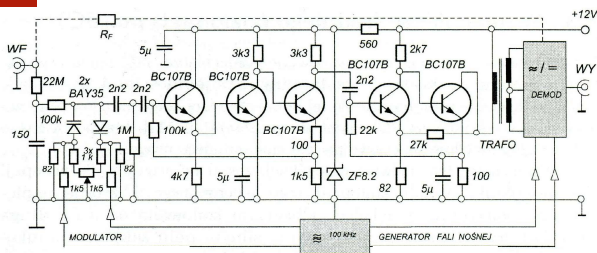
Parametric modulation



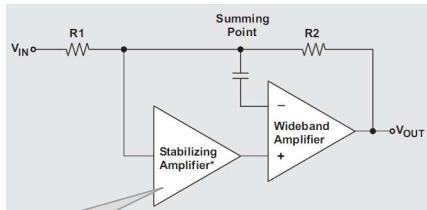
$$U_{MOD} = \frac{Q}{C} \approx \frac{C_0 U_{in}}{C_0 + \Delta C \sin \omega t} \approx \frac{U_{in}}{DC} - \frac{U_{in}}{AC} \frac{\Delta C}{C_0} \sin \omega t$$



Electrometer with parametric modulation



chopper -stabilized amp



chopper amp

auto-zero amp

phase 1

$$V_{C1} = V_{OSN} \left(\frac{A_N}{1 + B_N} \right)$$

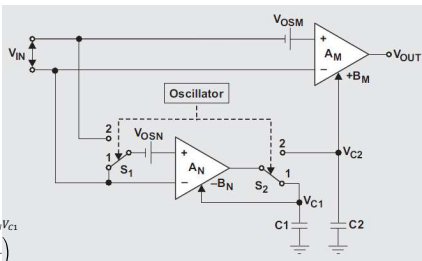
phase 2

$$V_{C2} = A_N(V_{IN} + V_{OSN}) - B_N V_{C1}$$

$$V_{C2} = A_N \left(V_{IN} + \frac{V_{OSN}}{1 + B_N} \right)$$

$$V_{OUT} = A_M(V_{IN} + V_{OSM}) + B_M V_{C2}$$

$$V_{OUT} = V_{IN}(A_M + A_N B_M) + V_{OSM} A_M + V_{OSN} \left(\frac{A_N B_M}{1 + B_N} \right) = V_{IN} A_N B_M \left(1 + \frac{A_M}{A_N B_M} + V_{OSM} \frac{A_M}{A_N B_M} + V_{OSN} \frac{1}{1 + B_N} \right)$$

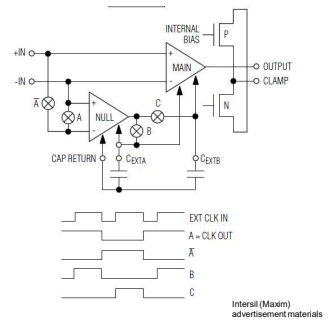


$$V_{OUT} = V_{IN}(A_M + A_N B_M) + V_{OSM} A_M + V_{OSN} \left(\frac{A_N B_M}{1 + B_N} \right) =$$

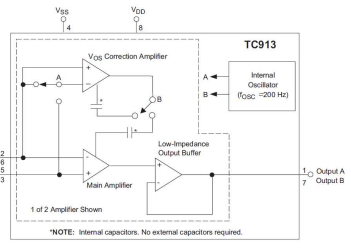
$$= V_{IN} A_N B_M \left(1 + \frac{A_M}{A_N B_M} + V_{OSM} \frac{A_M}{A_N B_M} + V_{OSN} \frac{1}{1 + B_N} \right) \approx$$

$$= V_{IN} A B + A(V_{OSM} + V_{OSN}) = A B \left(V_{IN} + \frac{V_{OSM} + V_{OSN}}{B} \right)$$

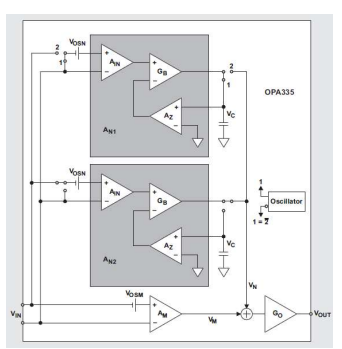
ICL7650



TC913



OPA335 wide band amp





Summary

- operational amplifier
 - ✓VV- voltage/voltage amp – review
 - ✓CV
 - ✓VC
 - ✓CC
- auto-zero amp
- electrometer
- charge amplifier
- choppered parametric modulation



Test questions:

1. The amplifier was designed for video signal using "current feedback amplifier". What is wrong with it ? (fig.b) ?
2. What are the VV, CC, CV, VC op-amp ?
3. Name the main parametres of a OpAmp.
4. What are the main features of a transconductance and a transimpedance amplifier?
5. What is the concept of a charge amplifier ?
6. What is the concept of a chopper amplifier ?
7. What is the idea of a parametric modulation amp ?

